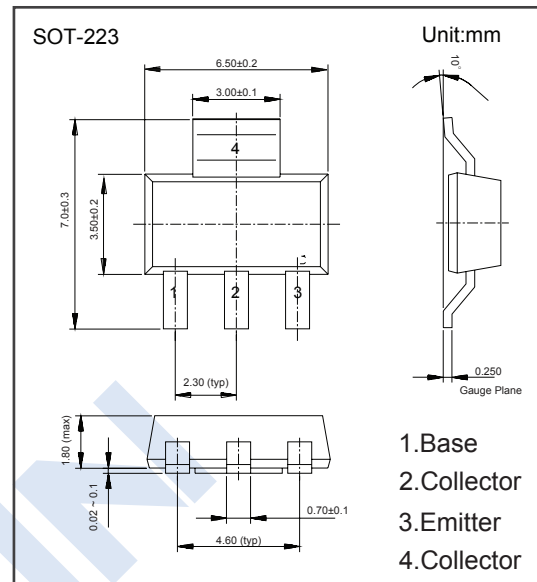


NPN Transistors

FZT655 (KZT655)

■ Features

- Low saturation voltage
- Complementary type FZT755



■ Absolute Maximum Ratings $T_a=25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	150	V
Collector - Emitter Voltage	V_{CE0}	150	V
Emitter - Base Voltage	V_{EB0}	5	V
Collector Current - Continuous	I_C	1	A
Peak Pulse Current	I_{CM}	2	A
Collector Power Dissipation	P_C	2	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

NPN Transistors

FZT655 (KZT655)

■ Electrical Characteristics Ta=25 °C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C =100 μA	150			V
Collector- emitter breakdown voltage	V _{CEO}	I _C =10 mA *	150			V
Emitter - base breakdown voltage	V _{EB0}	I _E =100 μA	5			V
Collector-base cut-off current	I _{CB0}	V _{CB} =125 V			0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} =3 V			0.1	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500 mA I _B =50 mA* I _C =1 A I _B =200 mA*			0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =500 mA I _B =50 mA*			1.1	V
Base - emitter turn-on voltage	V _{BE(on)}	I _C =500 mA V _{CE} =5 V *			1.0	V
DC current gain	h _{FE}	I _C =10 mA, V _{CE} =5V* I _C =500mA, V _{CE} =5V* I _C =1A, V _{CE} =5V*	50 50 20		300	
Output Capacitance	C _{ob}	V _{CB} =10 V f=1 MHz			20	pF
Transition frequency	f _T	I _C =10 mA, V _{CE} =20 V f=20 MHz	30			MHz

*Measured under pulsed conditions. Pulse Width =300 μs. Duty cycle ≤ 2 %

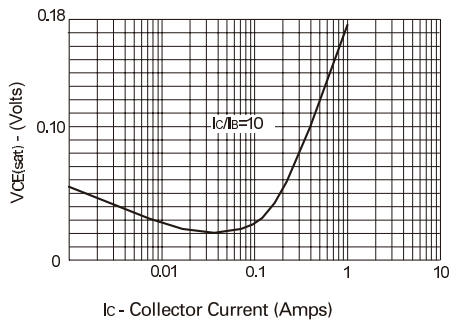
■ Marking

Marking	FZT655
---------	--------

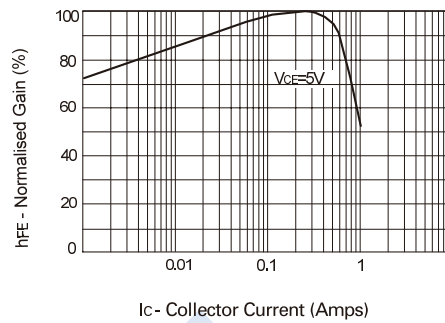
NPN Transistors

FZT655 (KZT655)

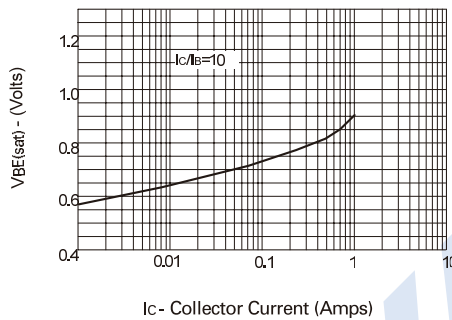
Typical Characteristics



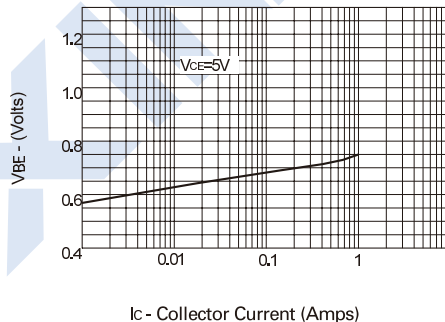
VCE(sat) v IC



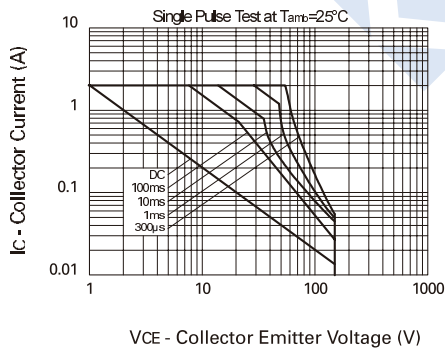
hFE v IC



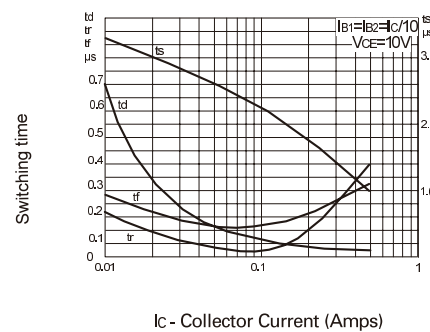
VBE(sat) v IC



VBE(on) v IC



Safe Operating Area



Switching Speeds